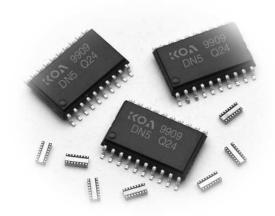




diode terminator network



This diode network is designed to provide nineteen channels of active termination for high-speed data signals to eliminate signal undershoot and overshoot. The network has the added benefit of acting to suppress any ESD voltage events by shunting the energy to ground assuring maximum reliability of electronic systems in the field. Trigger levels are defined by the positive and negative bias levels set by the user.

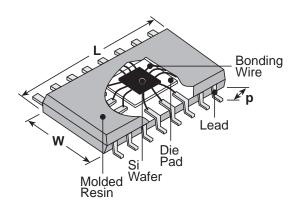
features

- Negligible reverse recovery time
- Low capacitance
- Low forward voltage drop
- 18-channel terminator in a single package
- Resolved bus impedance mismatch

applications

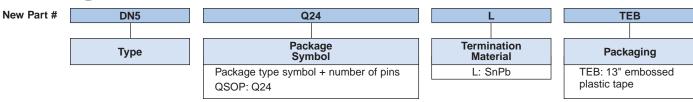
- Termination of data/control signals @ ≥ 66 MHz
- Dynamic RAM bus termination
- RISC architecture

dimensions and construction



Size	Dimensions inches (mm)				
Code	L	W	р		
Q24 .341 (8.66)		. 150 (3.81)	.033 (0.84)		

ordering information



For further information on packaging, please refer to Appendix C.

Specifications given herein may be changed at any time without prior notice. Please confirm technical specifications before you order and/or use.

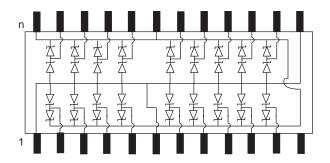
11/01/03



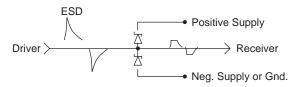


diode terminator network

circuit schematic



application schematic



n= number of pins (24)

applications and ratings

Part Designation	Forward Voltage	Reverse Breakdown Voltage	Leakage Current	Capacitance	Channel Clamp Voltage	ESD Voltage Capability	Operating Temperature Range	Supply Voltage (Vp ~ Vn)	Continuous Forward Current*	Total Power
DN5	0.6 to 0.95V	9.5 to 11V	1uA	2pF	±10V	16kV	-40°C to +85°C	8V	50mA	1W

^{*} One diode conducting

environmental applications

Performance Characteristics

Parameter	Maximum ∆ R	Test Method		
Resistance to Soldering Heat +0.25%		MIL-R-55342 4.7.7		
Short Time Overload	+0.50%	MIL-R-55342 4.7.5		
Moisture Resistance	+0.50%	MIL-STD-202 method 103		
Thermal Shock	+0.50%	MIL-STD-202 method 107		
H.A.S.T.	+1%	2 Atm., 121°C, 96 hrs		